



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

KTC4075 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.1 W ($T_{amb}=25$)

Collector current

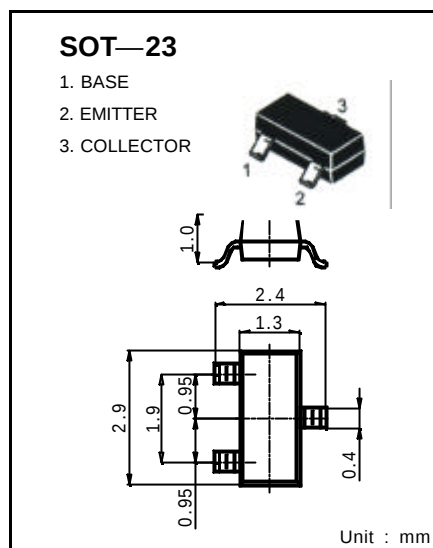
I_{CM} : 0.15 A

Collector-base voltage

$V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

T_J , T_{stg} : -55 to +150



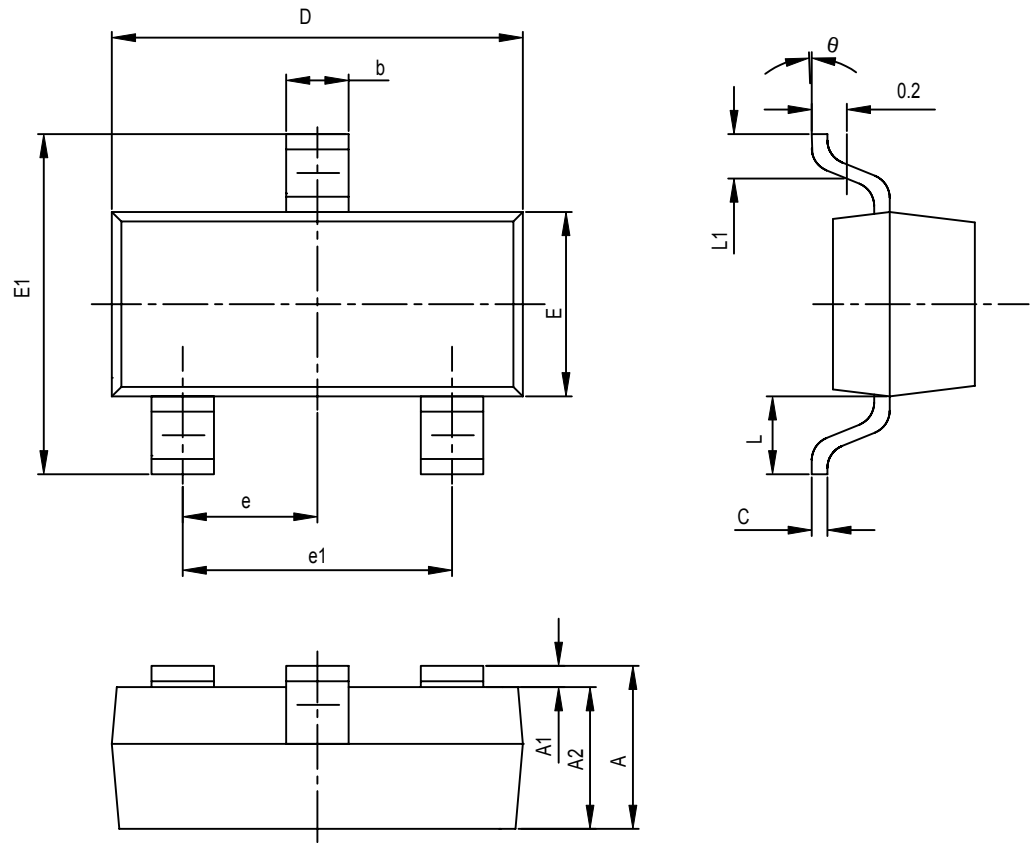
ELECTRICAL CHARACTERISTICS ($T_{amb}=25$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A$, $I_E = 0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA$, $I_B = 0$	50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A$, $I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 60V$, $I_E = 0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V$, $I_C = 0$		0.1	μA
DC current gain	h_{FE}	$V_{CE} = 6V$, $I_C = 2mA$	70	700	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 100mA$, $I_B = 10mA$		0.25	V
Transition frequency	f_T	$V_{CE} = 10V$, $I_C = 1mA$	80		MHz
Collector output capacitance	C_{ob}	$V_{CE} = 10V$, $I_E = 0$, $f = 1MHz$		3.5	dB
Noise figure	NF	$V_{CE} = 6V$, $I_E = 0.1mA$, $f = 1KHz$, $R_G = 10K\Omega$		10	dB

CLASSIFICATION OF h_{FE}

Rank	O	Y	GR	BL
Range	70~140	120~240	200~400	350~700
Marking	LO	LY	LGR	LBL

SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TPY		0.037TPY	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°